

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L^2 - π -MOSV)

2SK2614

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.032\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 8S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.)
($V_{DS} = 50V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0V$
($V_{DS} = 10V, I_D = 1mA$)

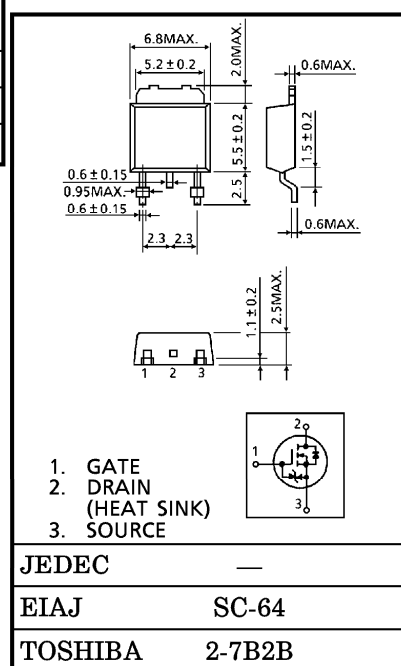
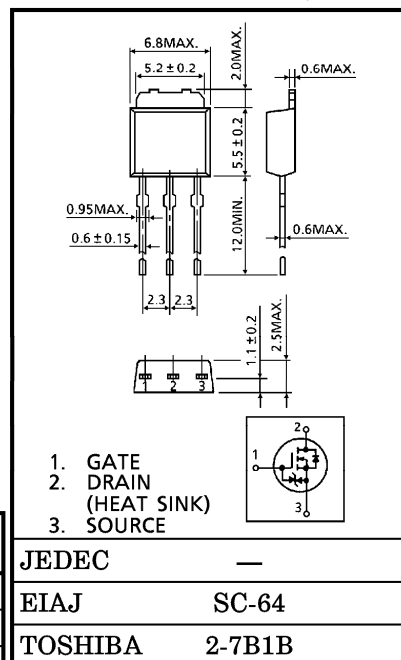
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	50	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	20	A
	Pulse	I_{DP}	50	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	40	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	125	$^\circ C / W$

This transistor is an electrostatic sensitive device.
Please handle with caution.

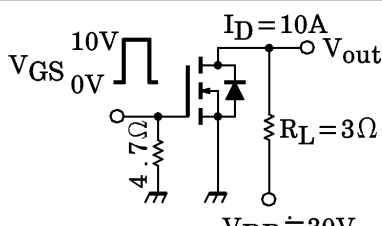


Weight : 0.36g

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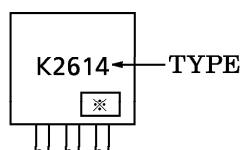
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GSS}	V _{GS} =±16V, V _{DS} =0V	—	—	±10	μA
Drain Cut-off Current		I _{DSS}	V _{DS} =50V, V _{GS} =0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	I _D =10mA, V _{GS} =0V	50	—	—	V
Gate Threshold Voltage		V _{th}	V _{DS} =10V, I _D =1mA	0.8	—	2.0	V
Drain-Source ON Resistance		R _{DS (ON)}	V _{GS} =4V, I _D =5A	—	0.055	0.08	Ω
			V _{GS} =10V, I _D =10A	—	0.032	0.046	
Forward Transfer Admittance		Y _{fs}	V _{DS} =10V, I _D =10A	7	13	—	S
Input Capacitance		C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	—	900	—	pF
Reverse Transfer Capacitance		C _{rss}		—	130	—	
Output Capacitance		C _{oss}		—	370	—	
Switching Time	Rise Time	t _r		—	15	—	ns
	Turn-on Time	t _{on}		—	25	—	
	Fall Time	t _f		—	30	—	
	Turn-off Time	t _{off}		—	100	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q _g	V _{DD} ≐40V, V _{GS} =10V, I _D =20A	—	25	—	nC
Gate-Source Charge		Q _{gs}		—	19	—	
Gate-Drain (“Miller”) Charge		Q _{gd}		—	6	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	20	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	50	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 20A, V_{GS} = 0V$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 20A, V_{GS} = 0V$	—	60	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	45	—	μC

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)